

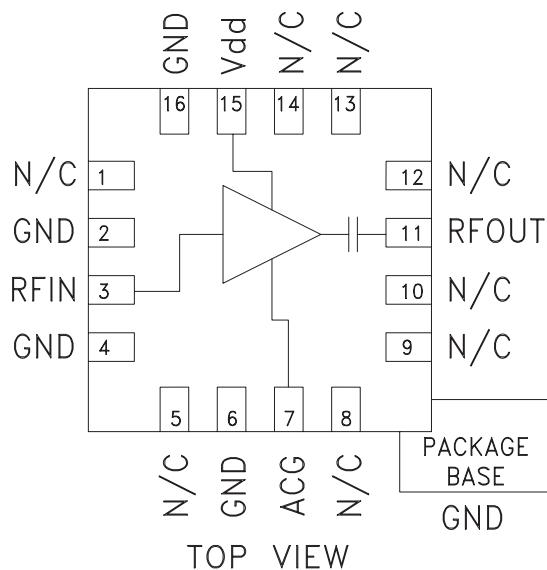


Typical Applications

The HMC356LP3 / HMC356LP3E is ideal for basestation receivers:

- GSM 450 & GSM 480
- CDMA 450
- Private Land Mobile Radio

Functional Diagram



Electrical Specifications, $T_A = +25^\circ C$, $V_s = +5V$

Parameter	Min.	Typ.	Max.	Units
Frequency Range		350 - 550		MHz
Gain	15	17		dB
Gain Variation Over Temperature		0.0032	0.010	dB / °C
Noise Figure		1.0	1.4	dB
Input Return Loss		17		dB
Output Return Loss		12		dB
Reverse Isolation		24		dB
Output Power for 1dB Compression (P1dB)	17	21		dBm
Saturated Output Power (Psat)		22.5		dBm
Output Third Order Intercept (IP3) (-20 dBm Input Power per tone, 1 MHz tone spacing)	34	38		dBm
Supply Current (Idd)		104		mA

HMC356* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS

View a parametric search of comparable parts.

EVALUATION KITS

- HMC356LP3 Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

- HMC356 Data Sheet

TOOLS AND SIMULATIONS

- HMC356 S-Parameter

REFERENCE MATERIALS

Quality Documentation

- Package/Assembly Qualification Test Report: 16L 3x3mm QFN Package (QTR: 11003 REV: 02)
- Package/Assembly Qualification Test Report: LP2, LP2C, LP3, LP3B, LP3C, LP3D, LP3F, LP3G (QTR: 2014-0364)
- Package/Assembly Qualification Test Report: Plastic Encapsulated QFN (QTR: 05006 REV: 02)
- Semiconductor Qualification Test Report: PHEMT-B (QTR: 2013-00233)

Technical Articles

- Active Multipliers & Dividers to Simplify Synthesizers

DESIGN RESOURCES

- HMC356 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

DISCUSSIONS

View all HMC356 EngineerZone Discussions.

SAMPLE AND BUY

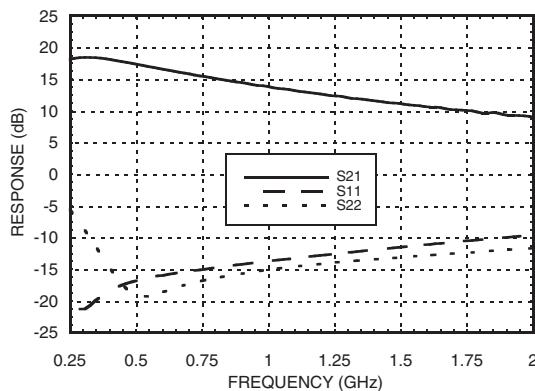
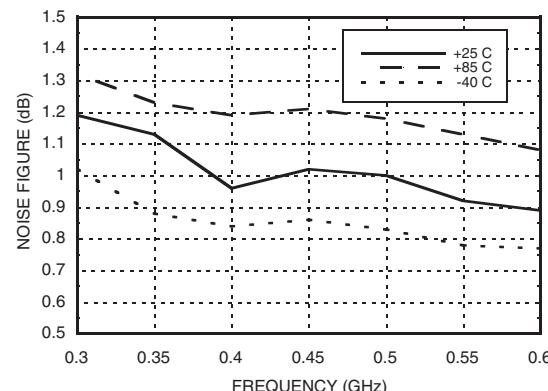
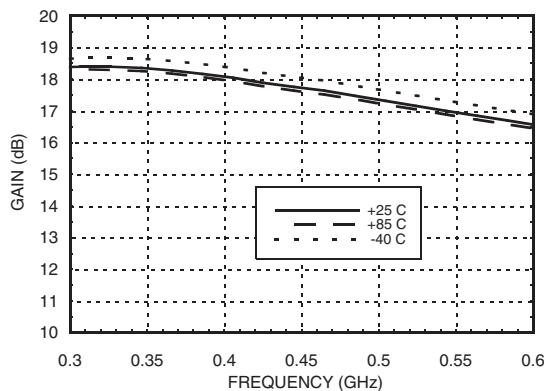
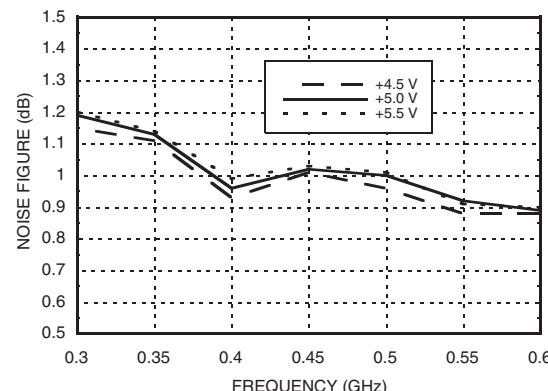
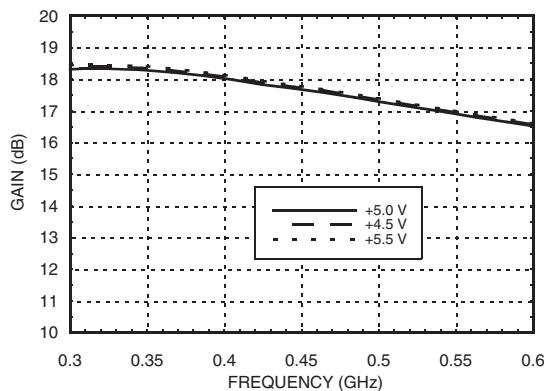
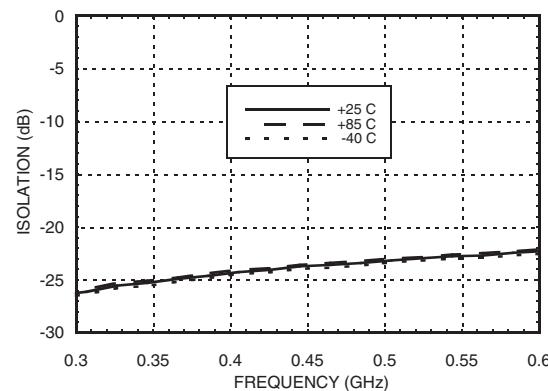
Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK

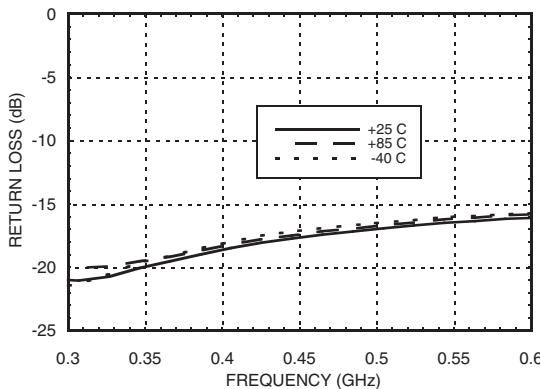
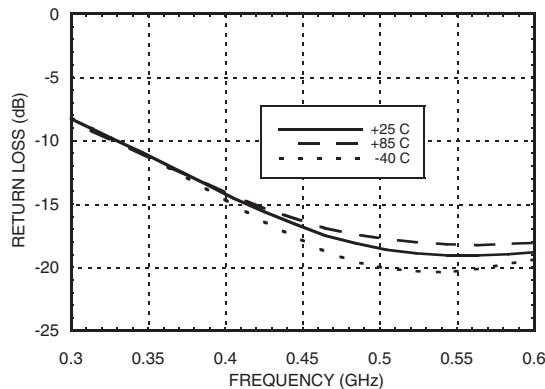
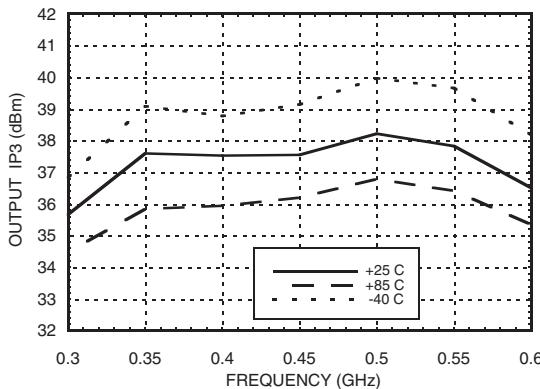
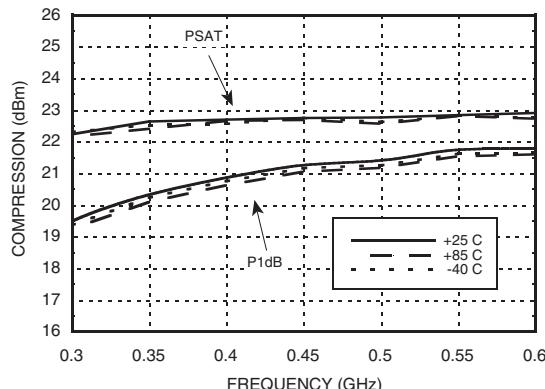
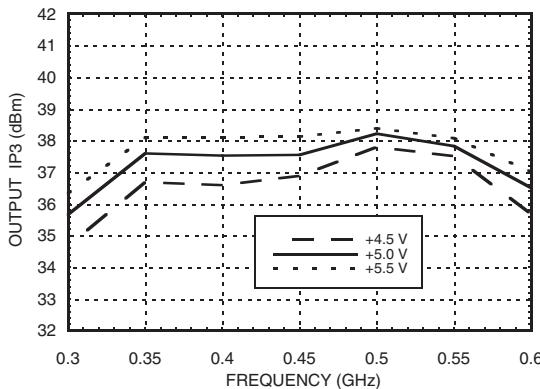
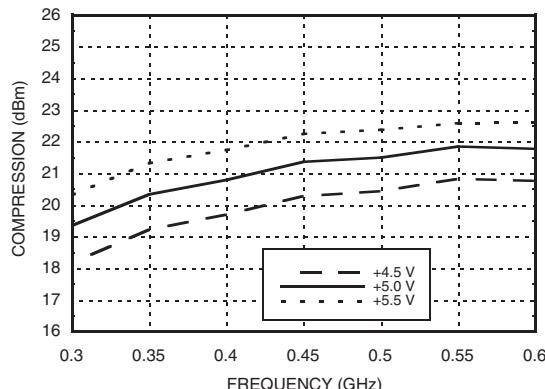
Submit feedback for this data sheet.


Broadband Gain & Return Loss

Noise Figure vs. Temperature

Gain vs. Temperature

Noise Figure vs. Vdd

Gain vs. Vdd

Reverse Isolation




HMC356LP3 / 356LP3E

**GaAs PHEMT MMIC LOW NOISE
AMPLIFIER, 350 - 550 MHz**

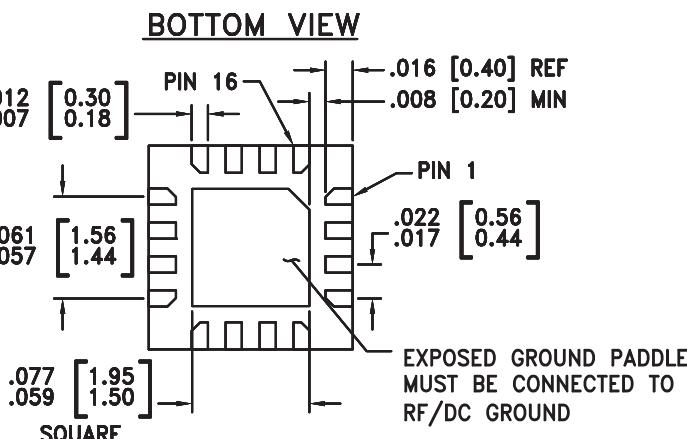
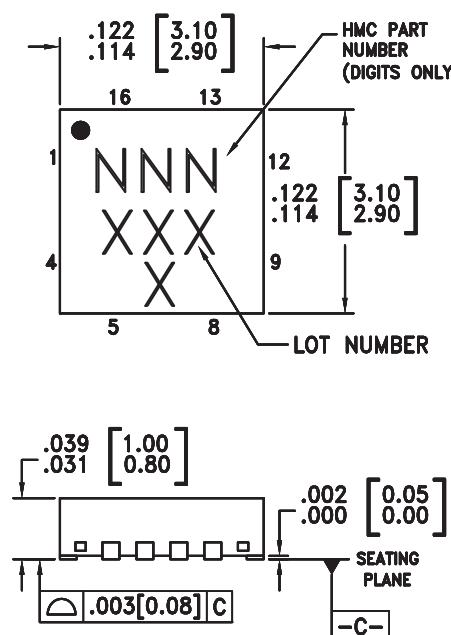
Input Return Loss vs. Temperature***Output Return Loss vs. Temperature******Output IP3 vs. Temperature******P1dB & Psat vs. Temperature******Output IP3 vs. Vdd******P1dB vs. Vdd***


Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+8.0 Vdc
RF Input Power (RFIN)(Vdd = +5.0 Vdc)	+15 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 14 mW/°C above 85 °C)	0.910 W
Thermal Resistance (channel to ground paddle)	71.4 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Typical Supply Current vs. Vdd

Vdd (Vdc)	Idd (mA)
+4.5	103
+5.0	104
+5.5	105


**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**
Outline Drawing

NOTES:

1. LEADFRAME MATERIAL: COPPER ALLOY
2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE
SOLDERED TO PCB RF GROUND.
7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED
LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC356LP3	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	356 XXXX
HMC356LP3E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	356 XXXX

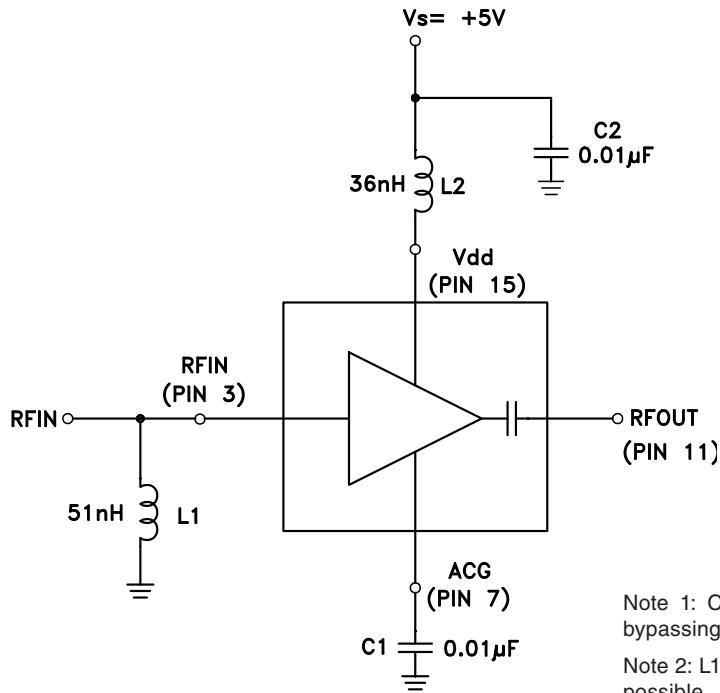
[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

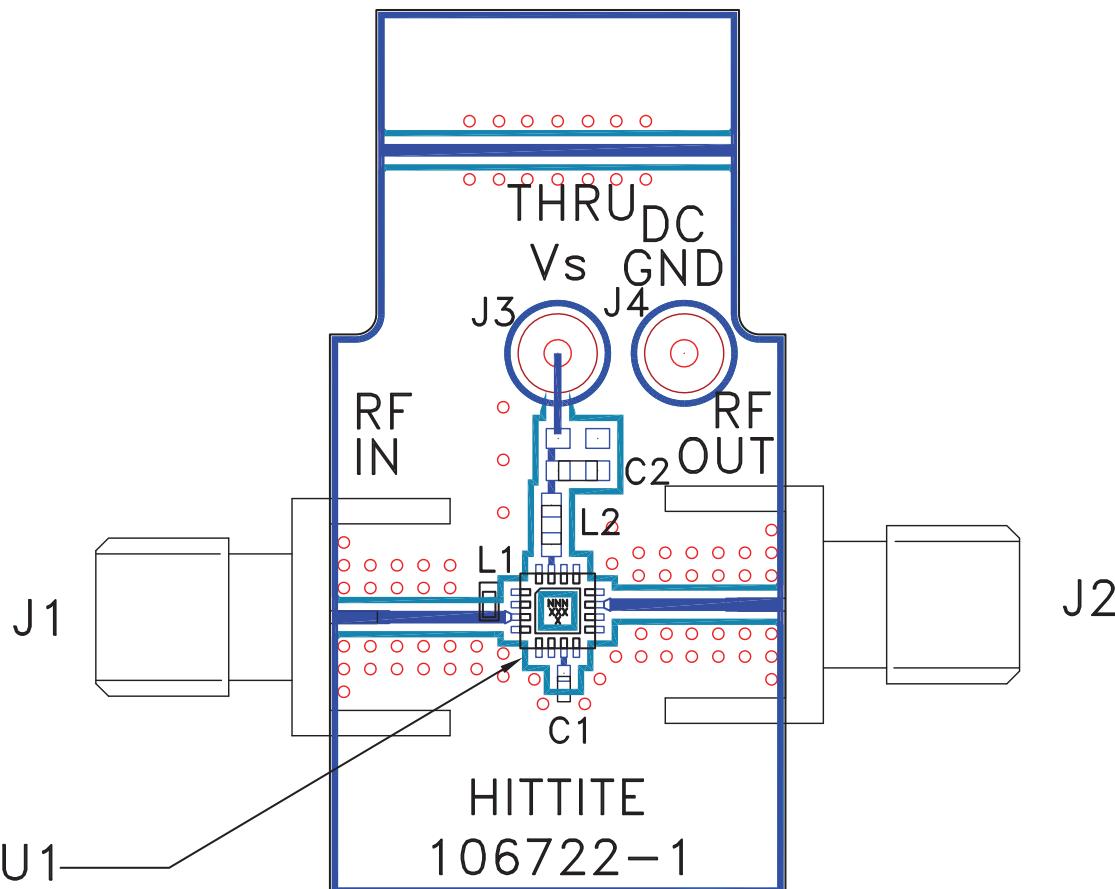

**GaAs PHEMT MMIC LOW NOISE
AMPLIFIER, 350 - 550 MHz**
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5, 8, 9, 10, 12, 13, 14	N/C	No connection necessary. These pins may be connected to RF/DC ground.	
2, 4, 6, 16	GND	These pins and package ground paddle must be connected to RF/DC ground.	
3	RFIN	This pin is matched to 50 Ohms with a 51 nH inductor to ground. See Application Circuit.	
7	ACG	AC Ground - An external capacitor of 0.01µF to ground is required for low frequency bypassing. See Application Circuit for further details.	
11	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
15	Vdd	Power supply voltage. Choke inductor and bypass capacitor are required. See application circuit.	

Application & Evaluation PCB Circuit


Note 1: Choose value of capacitor C1 for low frequency bypassing. A 0.01 µF ±10% capacitor is recommended.

Note 2: L1, L2 and C1 should be located as close to pins as possible.

Evaluation PCB

List of Materials for Evaluation PCB 107795 ^[1]

Item	Description
J1 - J2	PCB Mount SMA RF Connector
J3 - J4	DC Pin
C1	10,000 pF Capacitor, 0402 Pkg.
C2	10,000 pF Capacitor, 0603 Pkg.
L1	51 nH Inductor, 0402 Pkg.
L2	36 nH Inductor, 0603 Pkg.
U1	HMC356LP3 / HMC356LP3E Amplifier
PCB [2]	106722 Evaluation PCB

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Analog Devices Inc.:](#)

[HMC356LP3E](#) [HMC356LP3TR](#) [HMC356LP3ETR](#) [HMC356LP3](#) [107795-HMC356LP3](#)